





12V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	$11m\Omega @ V_{GS} = -4.5V$	-11A
-12V	14mΩ @ V _{GS} = -3.7V	-9.7A
	19mΩ @ V _{GS} = -2.5V	-8.3A
	30mΩ @ V _{GS} = -1.8V	-6.6A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Battery Management Application
- Power Management Functions
- DC-DC Converters

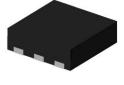
Features

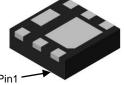
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

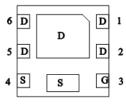
- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.007 grams (Approximate)

U-DFN2020-6 (Type F)

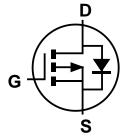




Top View Bottom View



Pin Out Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP1009UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel		
DMP1009UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



FZ = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	E		F	G		Н	ı		J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-12	V		
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Drain Current V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-11 -8.7	А
Continuous Drain Current V _{GS} = -4.5V (Note 6)	t<5s	$T_A = +25$ °C $T_A = +70$ °C	I _D	-15 -12	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-70	Α		
Maximum Body Diode Continuous Current (Note 6)	Is	-2.5	Α		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-24	А		
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	31	mJ		

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P _D	0.8	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Б	152	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	81	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P _D	2.0	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	63		
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	34	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	15		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)						•	
Gate Threshold Voltage	V _{GS(TH)}	-0.3	1	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			8.3	11		$V_{GS} = -4.5V, I_D = -5A$	
Static Drain-Source On-Resistance	D		9	14	mΩ	$V_{GS} = -3.7V, I_D = -5A$	
Static Dialii-Source Oil-Resistance	R _{DS(ON)}	_	12	19	11122	$V_{GS} = -2.5V, I_{D} = -4A$	
			16	30		$V_{GS} = -1.8V, I_D = -1A$	
Diode Forward Voltage	V _{SD}	_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	1860	_		10)/)/ 0)/	
Output Capacitance	Coss	_	498	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	416	_		1 – 1.01011 12	
Gate Resistance	R_g	_	11	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	26	_			
Total Gate Charge (V _{GS} = -8V)	Qg	_	44	_	nC	., ., ., ., .,	
Gate-Source Charge	Q _{gs}	_	3.3	_	IIC	$V_{DS} = -6V, I_{D} = -10A$	
Gate-Drain Charge	Q _{gd}	_	8.1	_			
Turn-On Delay Time	t _{D(ON)}	_	7.0	_			
Turn-On Rise Time	t _R	_	10.6	_		$V_{DS} = -6V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	62.2	_	ns	$R_G = 1\Omega$, $I_D = -8A$	
Turn-Off Fall Time	t _F	_	61	_			
Reverse Recovery Time	t _{RR}	_	34.4	_	ns	100 11/11 5000/	
Reverse Recovery Charge	Q _{RR}	_	28.1	_	nC	$I_F = -12A$, di/dt = 500A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

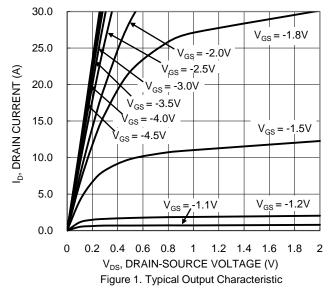
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

^{8.} Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.







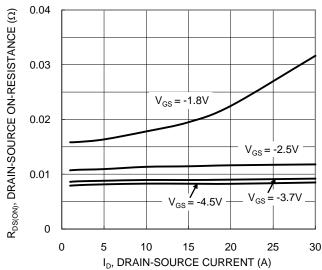


Figure 3. Typical On-Resistance vs. Drain Current and

Gate Voltage

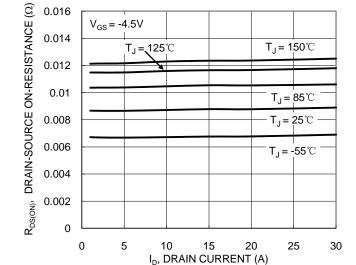


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

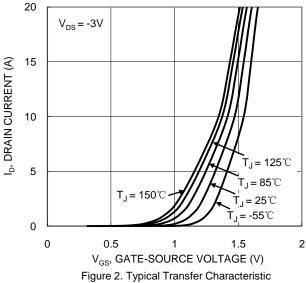
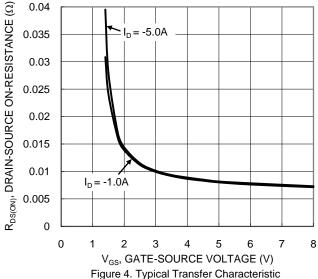


Figure 2. Typical Transfer Characteristic



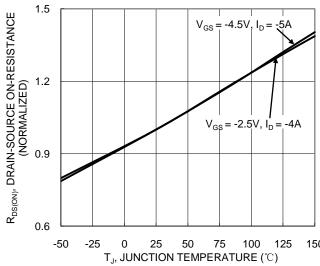


Figure 6. On-Resistance Variation with Temperature



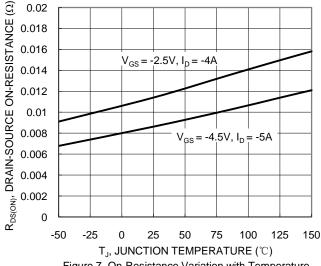


Figure 7. On-Resistance Variation with Temperature

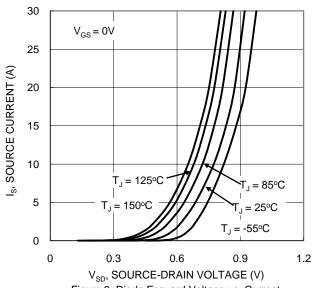
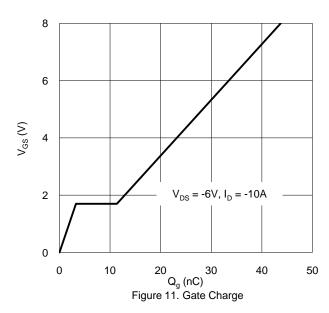


Figure 9. Diode Forward Voltage vs. Current



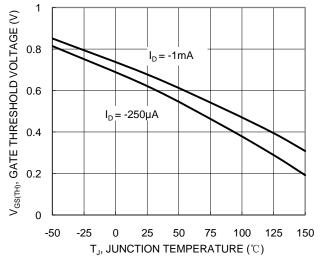
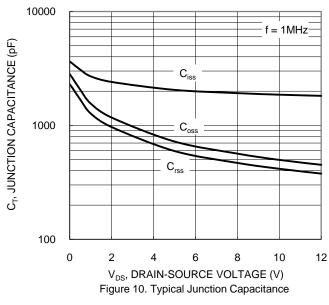
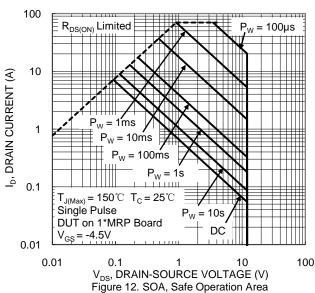


Figure 8. Gate Threshold Variation vs. Junciton Temperature







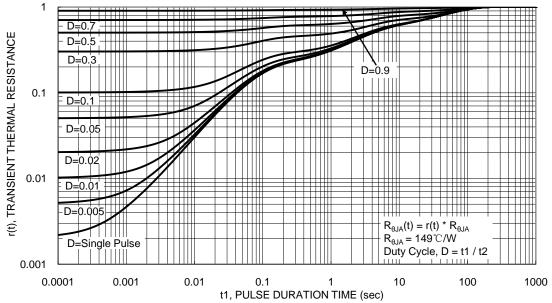


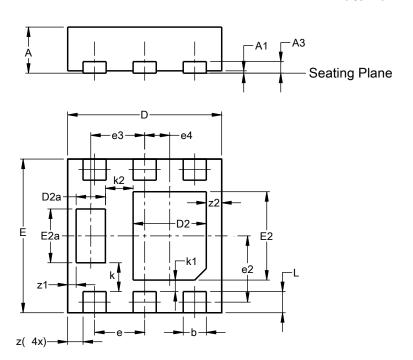
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

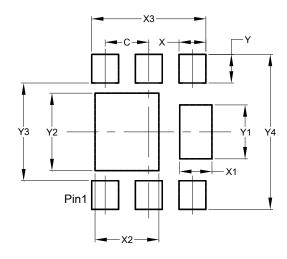


U-DFN2020-6								
(Type F)								
Dim	Min Max Typ							
Α	0.57	0.63	0.60					
A1	0.00	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.75	0.70					
е		0.65 BS	С					
e2).863 BS						
е3		0.70 BS						
e4	(0.325 BSC						
k	0.37 BSC							
k1	0.15 BSC							
k2	0.36 BSC							
L	0.225 0.325 0.275							
Z	0.20 BSC							
z 1	0.110 BSC							
z2	0.20 BSC							
All C	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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